
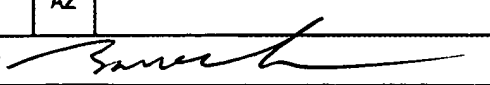


Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. <b>245469US2DIV</b>		SERIAL NO. <b>10/716,556</b>	
LIST OF REFERENCES CITED BY APPLICANT 				APPLICANT <b>Tadashi IGUCHI, et al.</b>			
				FILING DATE <b>November 20, 2003</b>		GROUP <b>2813</b>	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES      NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
~	AW	K. SHIMIZU, et al., "A Novel High-Density 5F <sup>2</sup> NAND STI Cell Technology Suitable for 256Mbit and 1Gbit Flash Memories", Microelectronics Engineering Laboratory, IEDM 97-271-274					
~	AX	Kenichi IMAMIYA, et al., "A 130-mm <sup>2</sup> , 256-Mbit NAND Flash with Shallow Trench Isolation Technology", IEEE Journal of Solid-State Circuits, vol. 34, no. 11, November 1999, pages 1536-1543					
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner 					Date Considered <b>11/1/03</b>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							